



# HCF4007UB

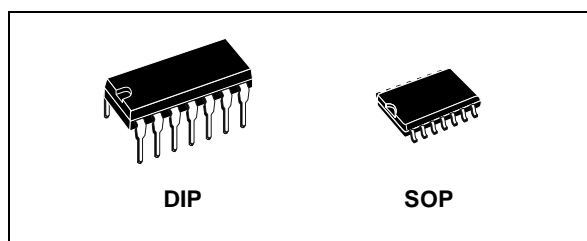
## DUAL COMPLEMENTARY PAIR PLUS INVERTER

- STANDARDIZED SYMMETRICAL OUTPUT CHARACTERISTICS
- MEDIUM SPEED OPERATION  
 $t_{PD} = 30\text{ns}$  (Typ.) AT 10V
- QUIESCENT CURRENT SPECIFIED UP TO 20V
- 5V, 10V AND 15V PARAMETRIC RATINGS
- INPUT LEAKAGE CURRENT  
 $I_I = 100\text{nA}$  (MAX) AT  $V_{DD} = 18\text{V}$   $T_A = 25^\circ\text{C}$
- 100% TESTED FOR QUIESCENT CURRENT

### DESCRIPTION

The HCF4007UB is a monolithic integrated circuit fabricated in Metal Oxide Semiconductor technology available in DIP and SOP packages.

The HCF4007UB type is comprised of three n-channel and three p-channel enhancement type MOS transistors. The transistor elements are accessible through the package terminals to provide a convenient means for constructing the various typical circuits as shown in typical

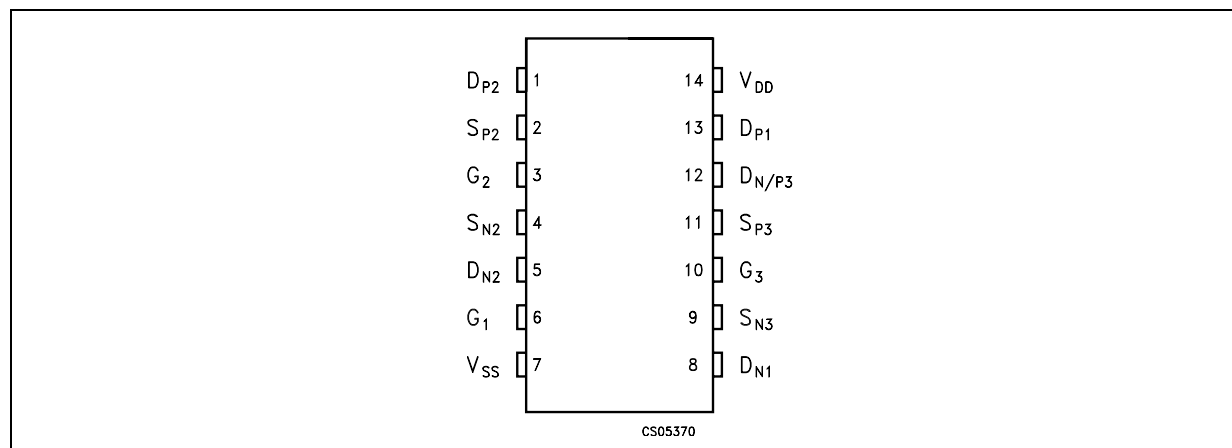


### ORDER CODES

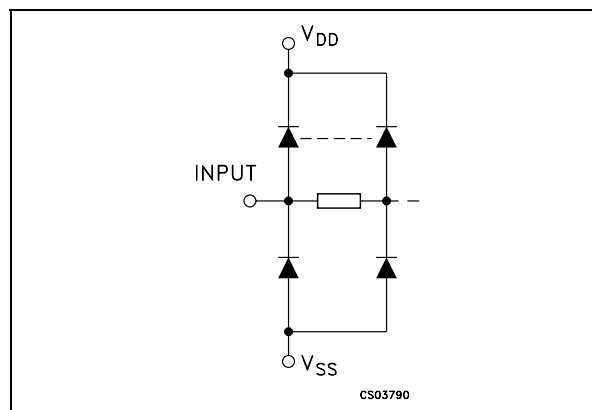
PACKAGE	TUBE	T & R
DIP	HCF4007UBEY	
SOP	HCF4007UBM1	HCF4007UM013TR

applications. More complex functions are possible using multiple packages. Number shown in parentheses indicate terminals that are connected together to form the various configuration listed.

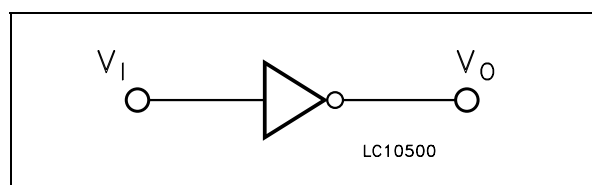
### PIN CONNECTION



## INPUT EQUIVALENT CIRCUIT



## LOGIC DIAGRAM



## PIN DESCRIPTION

PIN N°	SYMBOL	NAME AND FUNCTION
2, 11	$S_{P2}, S_{P3}$	Source Connections to 2nd and 3rd p-channel transistors
13, 1	$D_{P1}, D_{P2}$	Drain Connections from the 1st and 2nd p-channel transistors
8, 5	$D_{N1}, D_{N2}$	Drain Connections from the 1st and 2nd n-channel transistors
4, 9	$S_{N2}, S_{N3}$	Source Connections to the 2nd and 3rd n-channel
12	$D_{N/P3}$	Common connection to the 3rd p-channel and n-channel transistor drains
6, 3, 10	$G_1$ to $G_3$	Gate connections to n-channel and p-channel of the three transistor pairs
7	$V_{SS}$	Negative Supply Voltage
14	$V_{DD}$	Positive Supply Voltage

## ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
$V_{DD}$	Supply Voltage	-0.5 to +22	V
$V_I$	DC Input Voltage	-0.5 to $V_{DD} + 0.5$	V
$I_I$	DC Input Current	$\pm 10$	mA
$P_D$	Power Dissipation per Package	200	mW
	Power Dissipation per Output Transistor	100	mW
$T_{op}$	Operating Temperature	-55 to +125	°C
$T_{stg}$	Storage Temperature	-65 to +150	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied.

All voltage values are referred to  $V_{SS}$  pin voltage.

## RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
$V_{DD}$	Supply Voltage	3 to 20	V
$V_I$	Input Voltage	0 to $V_{DD}$	V
$T_{op}$	Operating Temperature	-55 to 125	°C

## DC SPECIFICATIONS

Symbol	Parameter	Test Condition				Value							Unit
		V <sub>I</sub> (V)	V <sub>O</sub> (V)	I <sub>O</sub>   (μA)	V <sub>DD</sub> (V)	T <sub>A</sub> = 25°C			-40 to 85°C		-55 to 125°C		
						Min.	Typ.	Max.	Min.	Max.	Min.	Max.	
I <sub>L</sub>	Quiescent Current	0/5			5		0.01	0.25		7.5		7.5	μA
		0/10			10		0.01	0.5		15		15	
		0/15			15		0.01	1		30		30	
		0/20			20		0.02	5		150		150	
V <sub>OH</sub>	High Level Output Voltage	0/5		<1	5	4.95			4.95		4.95		V
		0/10		<1	10	9.95			9.95		9.95		
		0/15		<1	15	14.95			14.95		14.95		
V <sub>OL</sub>	Low Level Output Voltage	5/0		<1	5		0.05			0.05		0.05	V
		10/0		<1	10		0.05			0.05		0.05	
		15/0		<1	15		0.05			0.05		0.05	
V <sub>IH</sub>	High Level Input Voltage		0.5/4.5	<1	5	4			4		4		V
			1/9	<1	10	8			8		8		
			1.5/13.5	<1	15	12.5			12.5		12.5		
V <sub>IL</sub>	Low Level Input Voltage		4.5/0.5	<1	5			1		1		1	V
			9/1	<1	10			2		2		2	
			13.5/1.5	<1	15			2.5		2.5		2.5	
I <sub>OH</sub>	Output Drive Current	0/5	2.5	<1	5	-1.36	-3.2		-1.15		-1.1		mA
		0/5	4.6	<1	5	-0.44	-1		-0.36		-0.36		
		0/10	9.5	<1	10	-1.1	-2.6		-0.9		-0.9		
		0/15	13.5	<1	15	-3.0	-6.8		-2.4		-2.4		
I <sub>OL</sub>	Output Sink Current	0/5	0.4	<1	5	0.44	1		0.36		0.36		mA
		0/10	0.5	<1	10	1.1	2.6		0.9		0.9		
		0/15	1.5	<1	15	3.0	6.8		2.4		2.4		
I <sub>I</sub>	Input Leakage Current	0/18	Any Input		18		±10 <sup>-5</sup>	±0.1		±1		±1	μA
C <sub>I</sub>	Input Capacitance		Any Input				5	7.5					pF

The Noise Margin for both "1" and "0" level is: 1V min. with V<sub>DD</sub>=5V, 2V min. with V<sub>DD</sub>=10V, 2.5V min. with V<sub>DD</sub>=15V

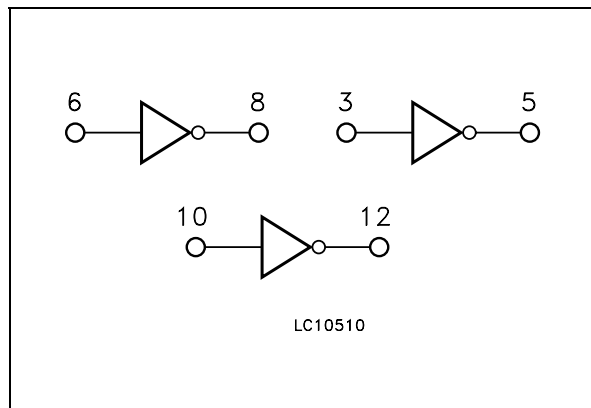
DYNAMIC ELECTRICAL CHARACTERISTICS (T<sub>amb</sub> = 25°C, C<sub>L</sub> = 50pF, R<sub>L</sub> = 200K $\Omega$ , t<sub>r</sub> = t<sub>f</sub> = 20 ns)

Symbol	Parameter	Test Condition		Value (*)			Unit
		V <sub>DD</sub> (V)		Min.	Typ.	Max.	
t <sub>PLH</sub> t <sub>PHL</sub>	Propagation Delay Time	5			55	110	ns
		10			30	60	
		15			25	50	
t <sub>TLH</sub> t <sub>THL</sub>	Transition Time	5			100	200	ns
		10			50	100	
		15			40	80	

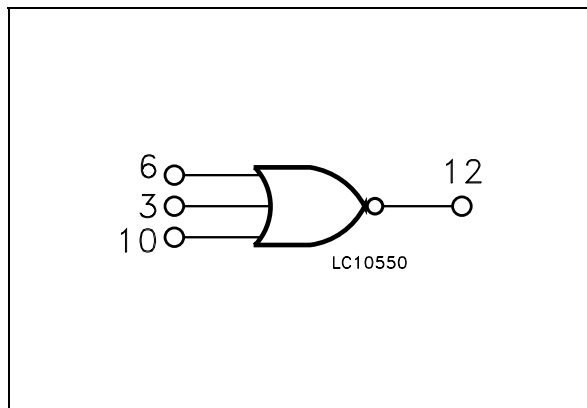
(\*) Typical temperature coefficient for all V<sub>DD</sub> value is 0.3%/°C.

## TYPICAL APPLICATIONS

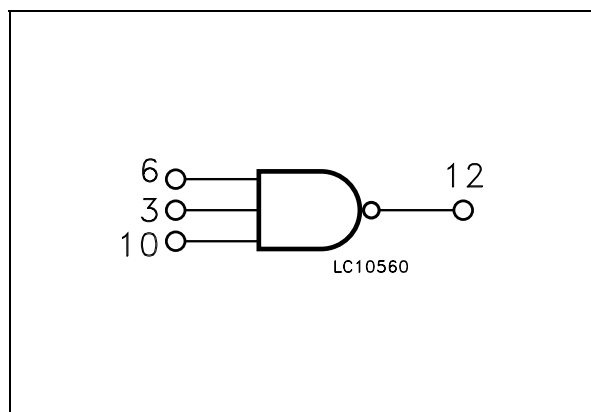
**TRIPLE INVERTERS:** (14, 2, 11); (8, 13); (1, 5); (4, 7, 9)



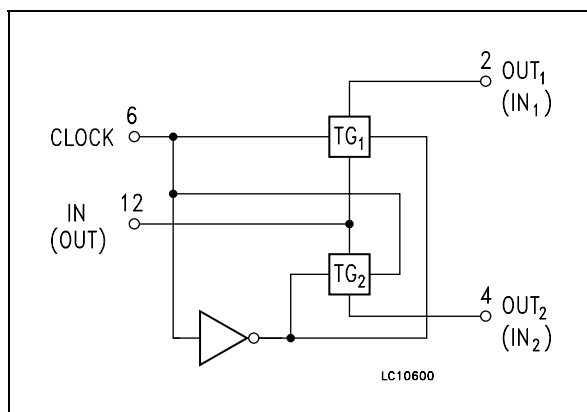
**3-INPUT NOR GATE:** (13, 2); (1, 11); (12, 5, 8); (4, 7, 9)



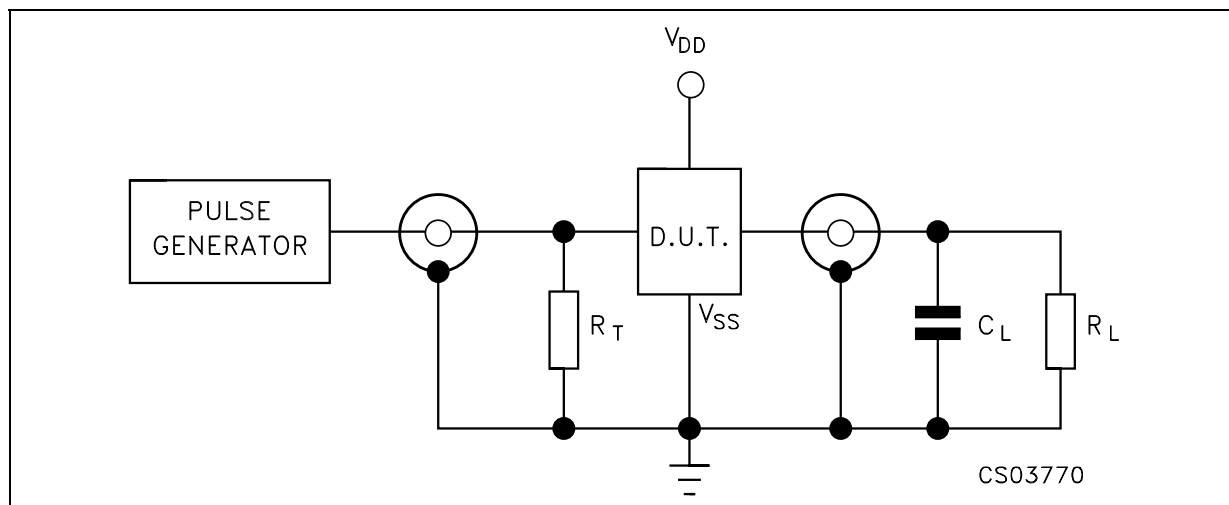
**3-INPUT NAND GATE:** (1, 12, 13); (2, 14, 11); (4, 8); (5, 9)



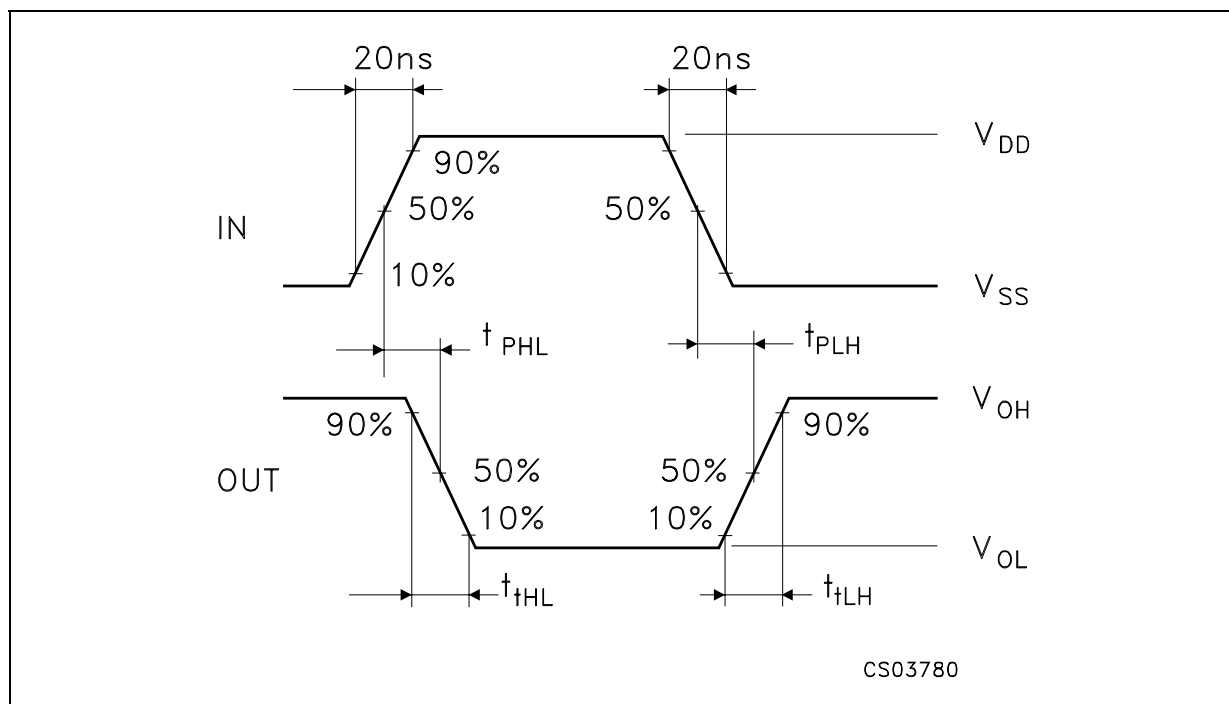
**DUAL BIDIRECTIONAL TRANSMISSION GATING:** (1, 5, 12); (2, 9); (11, 4); (8, 13, 10); (6, 3)



## TEST CIRCUIT

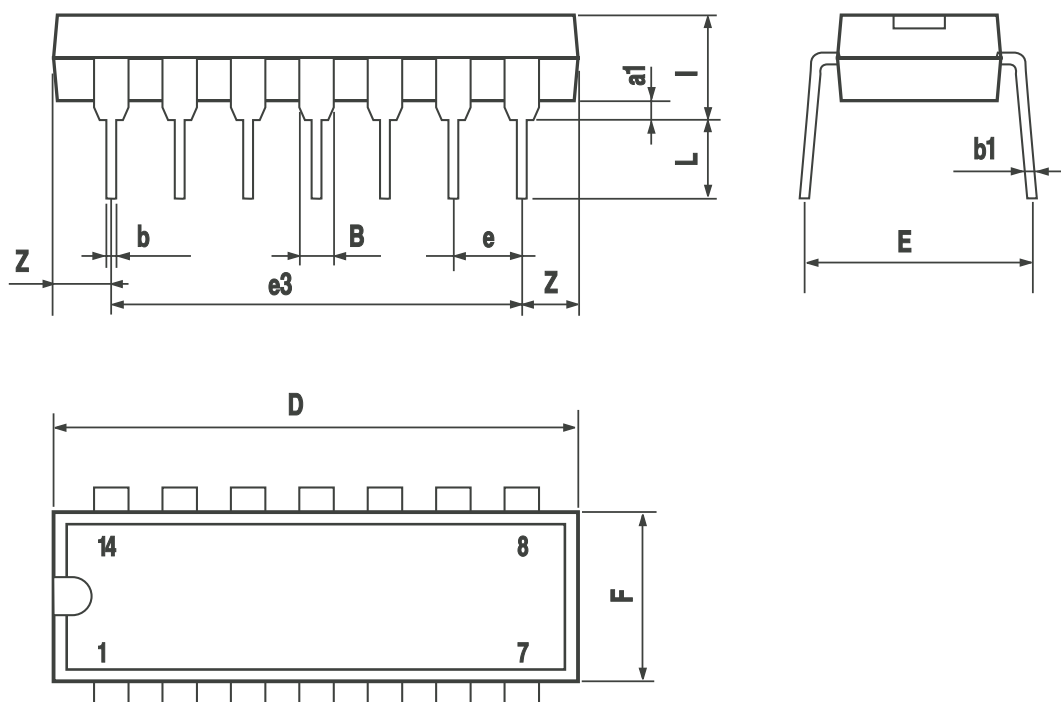


$C_L = 50\text{pF}$  or equivalent (includes jig and probe capacitance)  
 $R_L = 200\text{k}\Omega$   
 $R_T = Z_{\text{OUT}}$  of pulse generator (typically  $50\Omega$ )

WAVEFORM: PROPAGATION DELAY TIMES ( $f=1\text{MHz}$ ; 50% duty cycle)

## Plastic DIP-14 MECHANICAL DATA

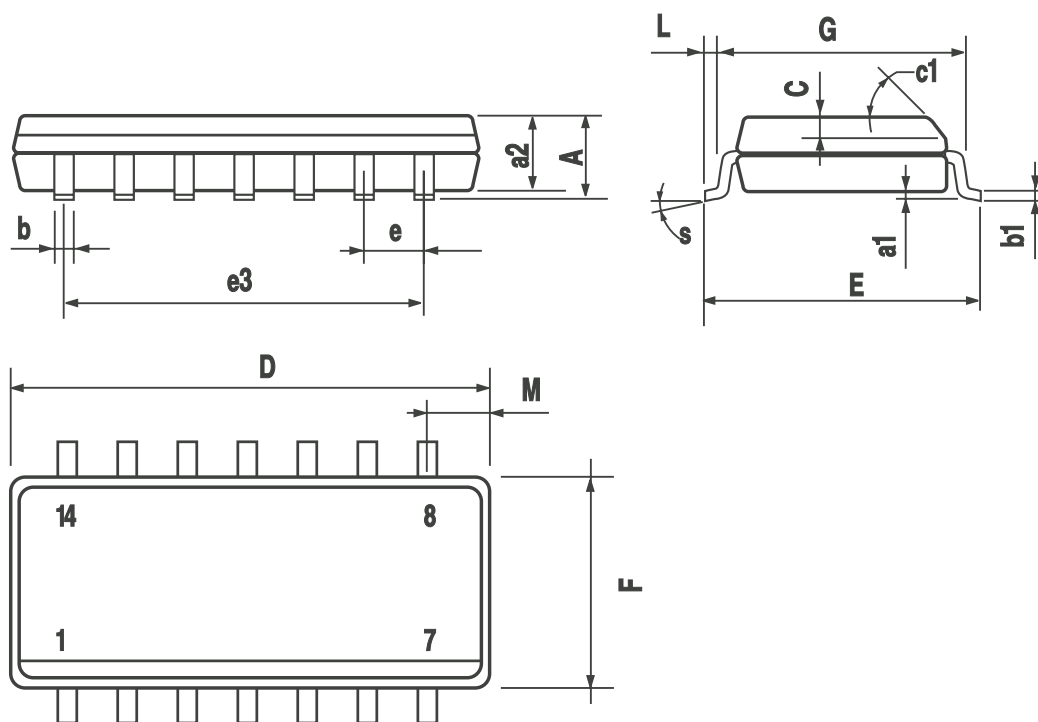
DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
a1	0.51			0.020		
B	1.39		1.65	0.055		0.065
b		0.5			0.020	
b1		0.25			0.010	
D			20			0.787
E		8.5			0.335	
e		2.54			0.100	
e3		15.24			0.600	
F			7.1			0.280
I			5.1			0.201
L		3.3			0.130	
Z	1.27		2.54	0.050		0.100



P001A

## SO-14 MECHANICAL DATA

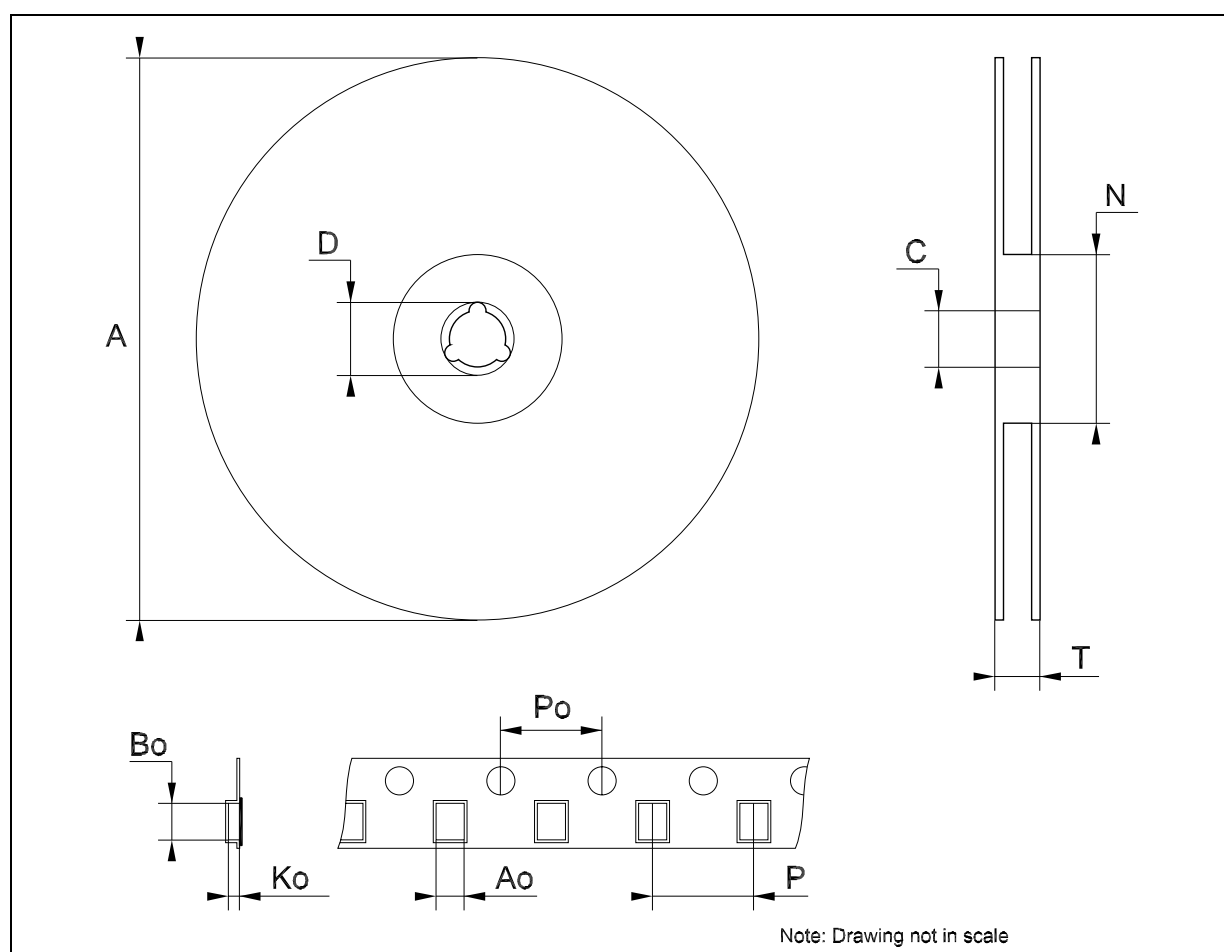
DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A			1.75			0.068
a1	0.1		0.2	0.003		0.007
a2			1.65			0.064
b	0.35		0.46	0.013		0.018
b1	0.19		0.25	0.007		0.010
C		0.5			0.019	
c1	45° (typ.)					
D	8.55		8.75	0.336		0.344
E	5.8		6.2	0.228		0.244
e		1.27			0.050	
e3		7.62			0.300	
F	3.8		4.0	0.149		0.157
G	4.6		5.3	0.181		0.208
L	0.5		1.27	0.019		0.050
M			0.68			0.026
S	8° (max.)					



PO13G

## Tape &amp; Reel SO-14 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A			330			12.992
C	12.8		13.2	0.504		0.519
D	20.2			0.795		
N	60			2.362		
T			22.4			0.882
Ao	6.4		6.6	0.252		0.260
Bo	9		9.2	0.354		0.362
Ko	2.1		2.3	0.082		0.090
Po	3.9		4.1	0.153		0.161
P	7.9		8.1	0.311		0.319





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